



UMC5N

DUAL COMPLEMENTARY PRE-BIASED TRANSISTORS

Features

- Epitaxial Planar Die Construction
- Surface Mount Package Suited for Automated Assembly
- Simplifies Circuit Design and Reduces Board Space
- Lead Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)

SOT353

Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

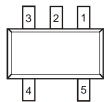
- Case: SOT353
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed Over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)

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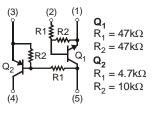


Top View

Bottom View



Package Pin Out Configuration



Device Schematic

Ordering Information (Note 3)

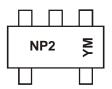
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Part Number	Case	Packaging
UMC5N-7	SOT353	3000/Tape & Reel

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.

3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



NP2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Key												
Year	2007	20	08	2009	2010	20	11	2012	2013	20	14	2015
Code	U	١	/	W	Х	Ň	(Z	А	E	3	С
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings, Pre-Biased NPN Transistor, Q1 @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	50	V
Input Voltage	V _{IN}	-10 to +40	V
Output Current	lo	30	mA
Collector Current	I _{C(MAX)}	100	mA

Maximum Ratings, Pre-Biased PNP Transistor, Q₂ @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	Vcc	-50	V
Input Voltage	V _{IN}	-20 to +7	V
Output Current	lo	-100	mA
Collector Current	I _{C(MAX)}	-100	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	PD	150	mW
Thermal Resistance, Junction to Ambient Air (Note 4)	R _{0JA}	833	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 4. Device mounted on FR-4 PCB; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com.

Electrical Characteristics, Pre-Biased NPN Transistor, Q1 @TA = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltage	(Note 5)	V _{I(OFF)}	0.5	_	—	V	$V_{CC} = 5V, I_{O} = 100\mu A$
input voltage	(Note 6)	VI(ON)	_	_	3	V	$V_0 = 0.3V, I_0 = 2mA$
Output Voltage		V _{O(ON)}	_	0.1	0.3	V	$I_0 / I_1 = 10 \text{mA} / 0.5 \text{ mA}$
Input Current		lı lı	_		0.18	mA	$V_I = 5V$
Output Current		I _{O(OFF)}	_		0.5	μA	$V_{CC} = 50V, V_1 = 0V$
DC Current Gain		Gı	68			_	$V_0 = 5V, I_0 = 5mA$
Gain-Bandwidth Product (Note 7)		fT	_	250		MHz	V _{CE} = 10V, I _E = -5mA, f = 100MHz
Input Resistance		R ₁	32.9	47	61.1	kΩ	
Resistance Ratio		R ₂ /R ₁	0.8	1	1.2		

5. The device is guaranteed to be in "OFF" state with $V_{I(OFF)}$ up to 0.5V 6. The device is guaranteed to be in "ON" state with $V_{I(ON)}$ starting from 3V

7. Characteristic of Transistor - for reference only.

Electrical Characteristics, Pre-Biased PNP Transistor, Q₂ @T_A = 25°C unless otherwise specified

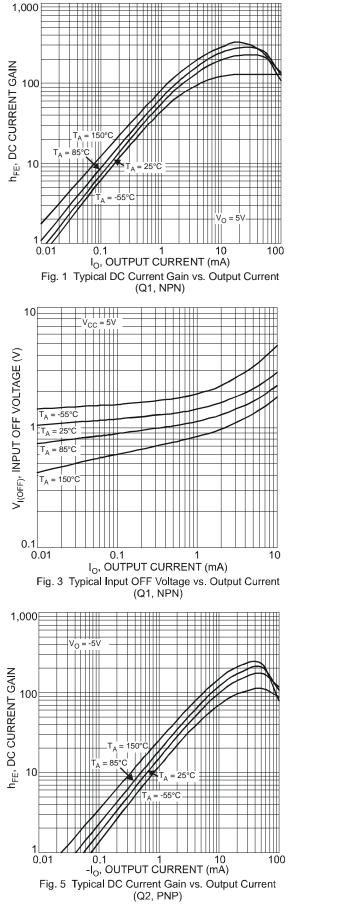
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
	V _{I(OFF)}	-0.3	_	_	V	$V_{CC} = -5V, I_{O} = -100\mu A$
Input Voltage	V _{I(ON)}	_		-2.5	V	$V_0 = -0.3V, I_0 = -20mA$
Output Voltage	V _{O(ON)}	_	-0.1	-0.3	V	I _O / I _I = -10mA/-0.5 mA
Input Current	li li	_		-1.8	mA	V _I = -5V
Output Current	I _{O(OFF)}	_	_	-0.5	μA	$V_{CC} = -50V, V_{I} = 0V$
DC Current Gain	GI	30		_	_	$V_0 = -5V, I_0 = -10mA$
Gain-Bandwidth Product (Note 7)	fT	_	250	_	MHz	V _{CE} = -10V, I _E = 5mA, f = 100MHz
Input Resistance	R ₁	3.29	4.7	6.11	kΩ	—
Resistance Ratio	R ₂ /R ₁	1.7	2.1	2.6	_	_

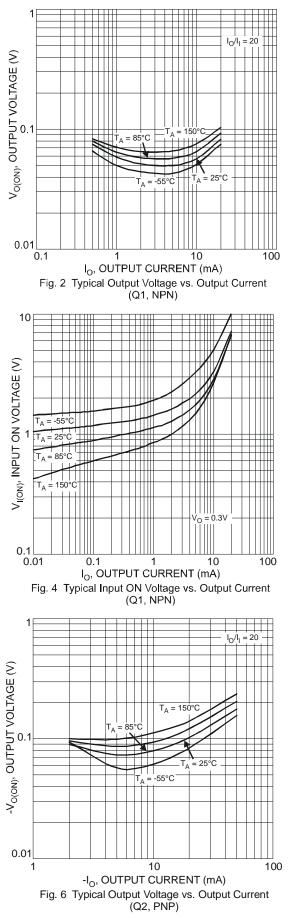
Notes: 8. The device is guaranteed to be in "OFF" state with $V_{\text{I(OFF)}}\,\text{up}$ to -0.3V

9. The device is guaranteed to be in "ON" state with VI(ON) starting from -2.5V 10. Characteristic of Transistor - for reference only.

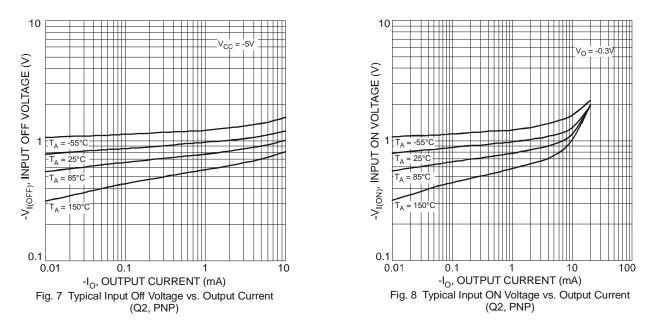
Notes:



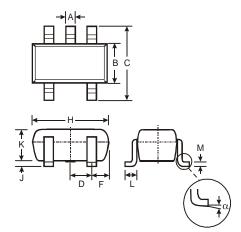






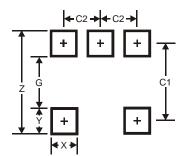


Package Outline Dimensions



SOT353						
Dim	Min	Max				
Α	0.10	0.30				
В	1.15 1.35					
С	2.00	2.20				
D	0.65 Typ					
F	0.40	0.45				
Н	1.80 2.20					
J	0 0.10					
К	0.90 1.00					
L	0.25 0.40					
М	0.10 0.22					
α	α 0° 8°					
All Di	mensions	in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65



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